

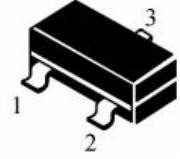


安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

1SS193/1SS181/1SS184/1SS226

SOT-23 Switching Diode 开关二极管



Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	1SS193	1SS181	1SS184	1SS226
Pin 管脚				
Mark 打标	F3	A3	B3	C3

Absolute Maximum Ratings 最大额定值

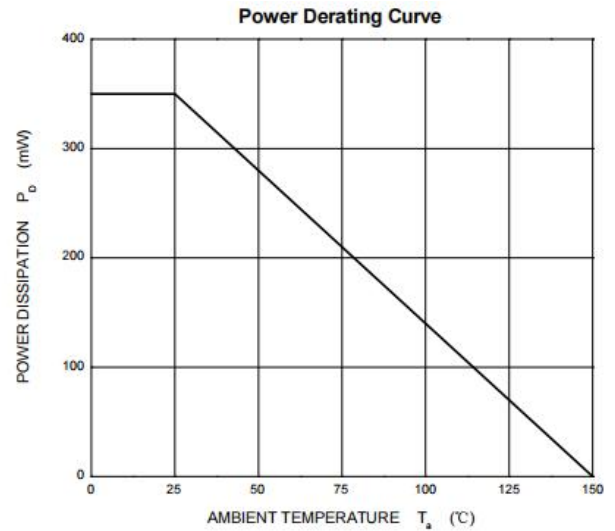
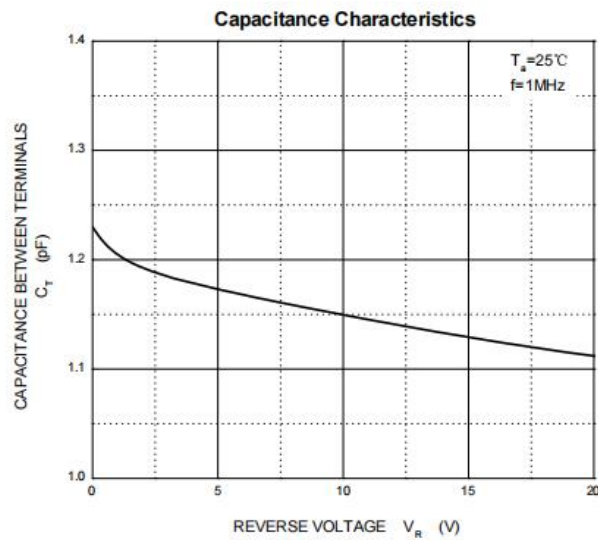
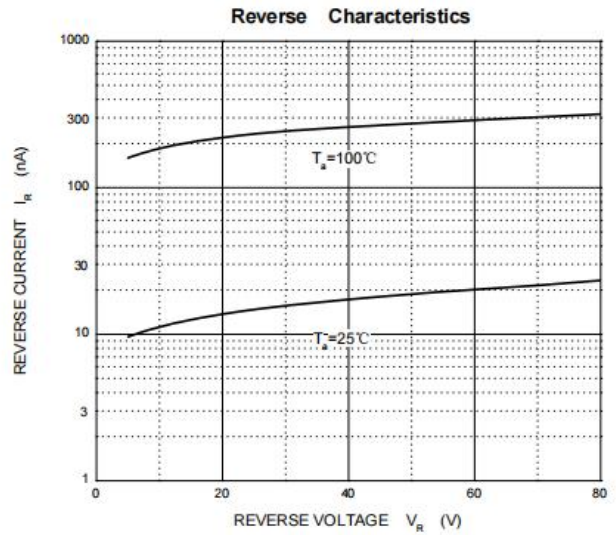
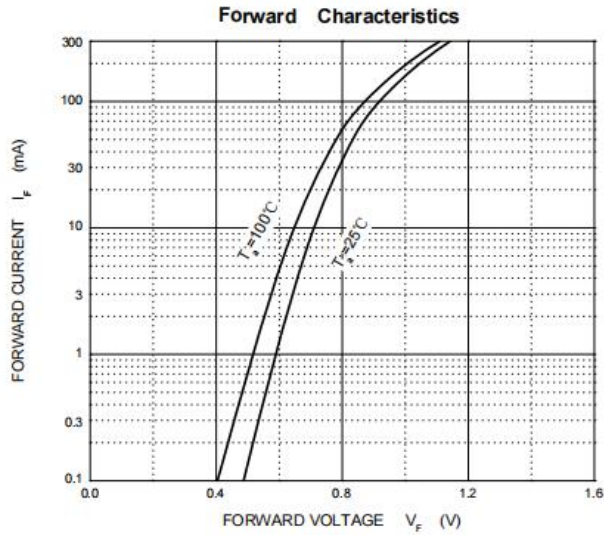
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	80	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	100	mA
Peak Forward Current 正向峰值电流	I_{FM}	300	mA
Power dissipation 耗散功率	$P_D(T_A=25^\circ\text{C})$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

Electrical Characteristics 电特性

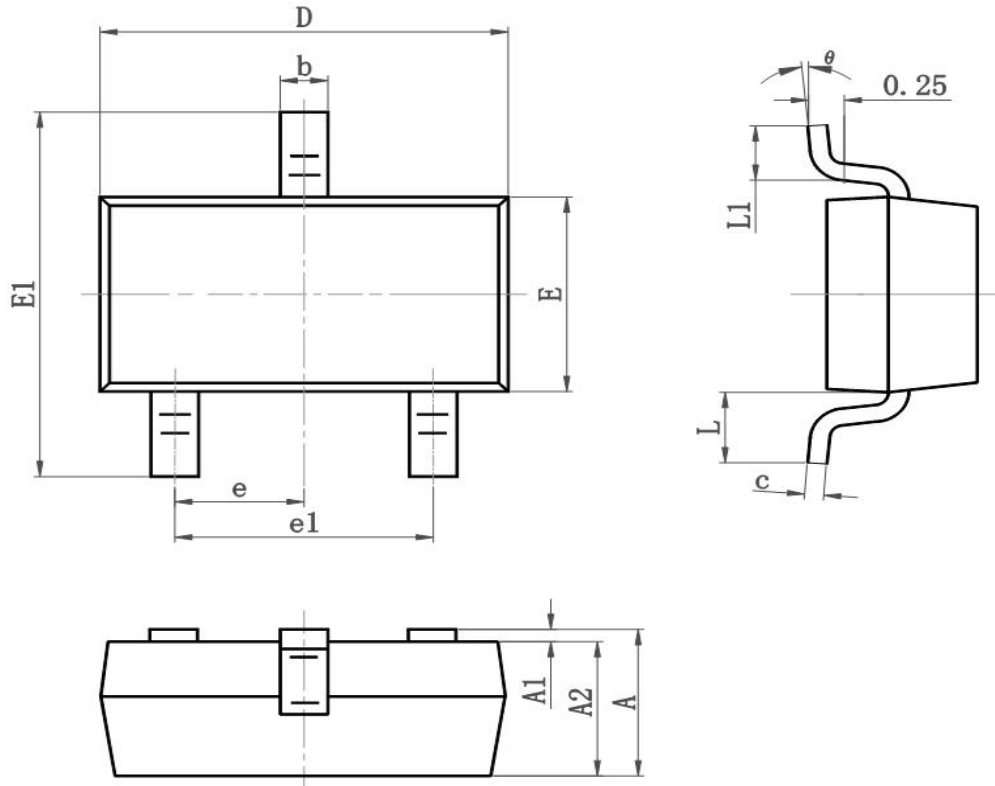
($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu\text{A}$)	$V_{(BR)}$	80	—	—	V
Reverse Leakage Current($V_R=30\text{V}$) 反向漏电流($V_R=80\text{V}$)	I_R	—	—	0.1 0.5	μA
Forward Voltage($I_F=1\text{mA}$) 正向电压($I_F=10\text{mA}$) ($I_F=100\text{mA}$)	V_F	—	0.61 0.74 0.92	1.2	V
Diode Capacitance 二极管电容($V_R=0\text{V}$, $f=1\text{MHz}$)	C_D	—	—	3	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	—	4	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°